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Attorney's Docket No.: 07977-107002 / US3194/3205/3215D1

#6/Amdt B
6.25.02
C. Wills

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Yamazaki, et al. Art Unit : 2812
Serial No.: 09/814,255 Examiner : Ori Nadav
Filed : March 21, 2001
Title : SEMICONDUCTOR DEVICE AND ITS MANUFACTURING METHOD

Commissioner for Patents
Washington, D.C. 20231

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RESPONSE

In response to the action mailed January 30, 2002, please
amend the application as follows:

In the claims:

Please cancel claims 3, 7, 10, 13, 16-18, 22, and 26.

Please amend claims 1, 5, 9, 12, 15, 20, and 24 as follows:

B1 Sub C2
1. (Amended) A semiconductor device comprising at least one
thin film transistor over a substrate, said thin film transistor
comprising:
a conductive layer comprising aluminum;
an insulating film formed on said conductive layer;
a contact hole formed through said insulating film;
a wiring electrically connected with said conductive layer
in said contact hole; and

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I hereby certify under 37 CFR §1.8(a) that this
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with sufficient postage on the date indicated
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5/29/2002

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